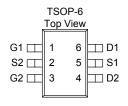
## N & P-Channel 40-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

•	Low r <sub>DS(on)</sub> provides higher efficiency and
	extends battery life

- Low thermal impedance copper leadframe TSOP-6 saves board space
- Fast switching speed
- High performance trench technology

PRODUCT SUMMARY							
$V_{DS}(V)$ $r_{DS(on)}(\Omega)$ $I_{D}(A)$							
40	$0.063 @V_{CS} = 10V$	3.7					
40	$0.082 @V_{CS} = 4.5V$	3.3					
-40	$0.172 @V_{CS} = -10V$	-2.7					
	$0.240 @V_{CS} = -4.5V$	-2.2					







ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED)									
Parameter	Symbol	N-Channel	P-Channel	Units					
Drain-Source Voltage			40	-40	V				
Gate-Source Voltage	$V_{GS}$	±20	±20	V					
	$T_A=25^{\circ}C$	T	3.7	-2.7					
Continuous Drain Current <sup>a</sup>	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	$I_{\mathrm{D}}$	2.9	-2.1	Α				
Pulsed Drain Current <sup>b</sup>	$I_{DM}$	8	-8						
Continuous Source Current (Diode Conduc	$I_S$	1.05	-1.05	A					
D a	$T_A=25^{\circ}C$	1.15		15	W				
Power Dissipation <sup>a</sup>	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	$P_{\rm D}$	0.7		W				
Operating Junction and Storage Temperature Range			-55 to	°C					

THERMAL RESISTANCE RATINGS								
Domomotou	Symbol	N-Channel		P-Channel		TI:4		
Parameter		Тур	Max	Тур	Max	Unit		
Mariana Innation to Analysis a	t <= 10 sec	D	93	110	93	110	°C/W	
Maximum Junction-to-Ambient <sup>a</sup>	Steady State	$R_{thJA}$	130	150	130	150	C/W	

## Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

AM3548C

Davis4	C11	Took Co. 3'4'		Li	mits		TT		
Parameter	Symbol	<b>Test Conditions</b>	Ch	Min	Тур	Max	Unit		
Static									
Gate-Threshold Voltage	$V_{GS(th)}$	VGS = VDS, $ID = 250  uA$	N	1			V		
Gate-Tilleshold Voltage	V GS(th)	VGS = VDS, $ID = -250  uA$	P	-1			<b>'</b>		
Gate-Body Leakage Current	$I_{GSS}$	VDS = 0 V, $VGS = 20 V$	N			100	uA		
Gate-Body Leakage Current	1055	$V_{DS} = 0 \text{ V}, V_{GS} = -20 \text{ V}$	P			-100	uA		
		VDS = 32  V, VGS = 0  V	N			1	uA		
Zero Gate Voltage Drain Current	$I_{DSS}$	VDS = -32  V, VGS = 0  V	P			-1	uA		
Zero Gate Voltage Diam Current	1088	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ} \text{C}$	N			10	uA		
		$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$	P			-10	uz t		
On-State Drain Current <sup>A</sup>	ī	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	N	5			_		
On-State Drain Current	$I_{D(on)}$	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	P	-5			A		
		VGS = 10  V, ID = 3.7  A	N			0.063			
Drain-Source On-Resistance <sup>A</sup>		VGS = -10  V, ID = 3.1  A	P			0.172	Ω		
Diam-Source On-Resistance	$r_{\mathrm{DS(on)}}$	VGS = 4.5  V, ID = 3.3  A	N			0.082	52		
		VGS = -4.5  V, ID = -2.2  A	P			0.240			
Forward Tranconductance <sup>A</sup>	$\mathbf{g}_{\mathrm{fs}}$	$V_{DS} = 5 \text{ V}, I_D = 3.7 \text{ A}$	N		10		S		
Forward Tranconductance	SIS	$V_{DS} = -5 \text{ V}, I_D = 3.1 \text{ A}$	P		5		3		
D: 1 E 1W 1 A	V	$I_S = 1.05 \text{ A}, V_{GS} = 0 \text{ V}$	N		0.80		S		
Diode Forward Voltage <sup>A</sup>	$ m V_{SD}$	$I_S = -1.05 \text{ A}, V_{GS} = 0 \text{ V}$	P		-0.83		5		
Dynamic <sup>b</sup>							•		
Total Gate Charge	$Q_g$		N		2.2				
Total Gate Charge	Qg	N-Channel P	P		3.8		]		
Gate-Source Charge	$Q_{gs}$	$V_{DS}$ =15V, $V_{GS}$ =4.5V, $I_{D}$ =2.7A N	0.5		пC				
dute Bource Charge	₹gs	P-Channel	P		0.6		110		
Gate-Drain Charge	$Q_{\mathrm{ed}}$	VDS=-15V, VGS=-4.5V, ID=-3.1A	N		0.8				
	₹gu		P		1.5				
Turn-On Delay Time	$t_{d(on)}$		N		5		4		
	t <sub>r</sub>	N-Chaneel	P		12		1		
Rise Time		$V_{DD}$ =15V, VGS=4.5V, ID=1A, $R_{GEN}$ =15 $\Omega$ ,	N P		15		nS		
		P-Channel	N		13				
Turn-Off Delay Time	$t_{d(off)}$	VDD=-15V, VGS=-4.5V, ID=-1A	P		20				
		RGEN=15 $\Omega$	N		7				
Fall-Time	$t_{\mathrm{f}}$		P		20		1		

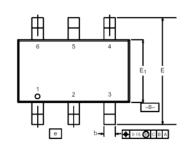
## Notes

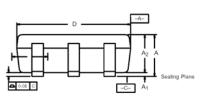
- a. Pulse test:  $PW \le 300us duty cycle \le 2\%$ .
- b. Guaranteed by design, not subject to production testing.

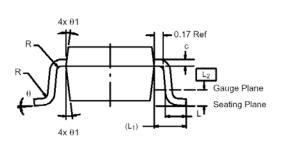
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## Package Information

TSOP-6: 6LEAD







	MIL	LIMET	ERS	INCHES				
Dim	Min	Nom	Max	Min	Nom	Max		
Α	0.91	-	1.10	0.036	-	0.043		
A <sub>1</sub>	0.01	_	0.10	0.0004	_	0.004		
A <sub>2</sub>	0.84	_	1.00	0.033	0.038	0.039		
b	0.30	0.32	0.45	0.012	0.013	0.018		
С	0.10	0.15	0.20	0.004	0.006	0.008		
D	2.95	3.05	3.10	0.116	0.120	0.122		
E	2.70	2.85	2.98	0.106	0.112	0.117		
E <sub>1</sub>	1.55	1.65	1.70	0.061	0.065	0.067		
е		1.00 BSC		0.0394 BSC				
L	0.35	_	0.50	0.014	-	0.020		
L <sub>1</sub>		0.60 Ref		0.024 Ref				
L <sub>2</sub>		0.25 BSC		0.010 BSC				
R	0.10	_	_	0.004	_	_		
θ	0°	4°	8°	0°	4°	8°		
$\theta_1$		7° Nom			7° Nom			